NSN 5961-01-124-2496

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View Online at https://aerobasegroup.com/nsn/5961-01-124-2496 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.450 inches Overall Diameter: 0.875 inches **End Application:** An/uyq-10 e/i fscm 54779 **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 breakdown voltage, collector-to-base, emitter open and 100.0 breakdown voltage, collector-to-emitter, base open and -5.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 120.00 milliamperes source cutoff current and 8.00 amperes source cutoff current **Power Rating Per Characteristic:** 100.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 1 case and 2 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Fiig: A110a0

No